



# 2SJ217

## Silicon P Channel MOS FET

REJ03G0850-0200  
(Previous: NON-084)  
Rev.2.00  
Sep 07, 2005

### Description

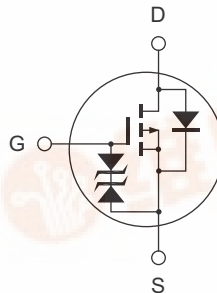
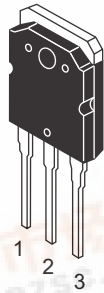
High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

### Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name: TO-3P)



1. Gate
2. Drain (Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	-60	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	-45	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	-180	A
Body to drain diode reverse drain current	I <sub>DR</sub>	-45	A
Channel dissipation	P <sub>ch</sub> <sup>Note 2</sup>	150	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at Tc = 25°C

## Electrical Characteristics

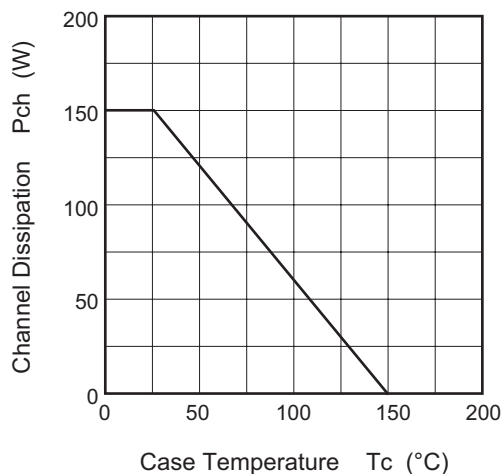
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	-60	—	—	V	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR) GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	-250	μA	V <sub>DS</sub> = -50 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	-1.0	—	-2.0	V	I <sub>D</sub> = -1 mA, V <sub>DS</sub> = -10 V
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	0.033	0.042	Ω	I <sub>D</sub> = -20 A, V <sub>GS</sub> = -10 V <sup>Note 3</sup>
	R <sub>DS (on)</sub>	—	0.045	0.06	Ω	I <sub>D</sub> = -20 A, V <sub>GS</sub> = -4 V <sup>Note 3</sup>
Forward transfer admittance	y <sub>fs</sub>	16	25	—	S	I <sub>D</sub> = -20 A, V <sub>DS</sub> = -10 V <sup>Note 3</sup>
Input capacitance	C <sub>iss</sub>	—	3800	—	pF	V <sub>DS</sub> = -10 V
Output capacitance	C <sub>oss</sub>	—	2000	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	C <sub>rss</sub>	—	490	—	pF	f = 1 MHz
Turn-on delay time	t <sub>d (on)</sub>	—	30	—	ns	I <sub>D</sub> = -20 A V <sub>GS</sub> = -10 V R <sub>L</sub> = 1.5 Ω
Rise time	t <sub>r</sub>	—	235	—	ns	
Turn-off delay time	t <sub>d (off)</sub>	—	670	—	ns	
Fall time	t <sub>f</sub>	—	450	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	-1.35	—	V	I <sub>F</sub> = -45 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	300	—	ns	I <sub>F</sub> = -45 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 50 A/μs

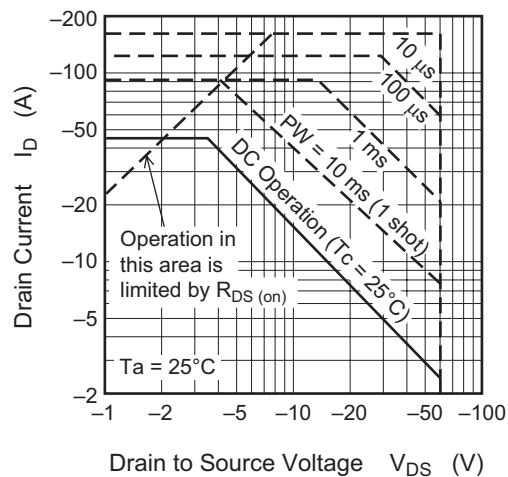
Note: 3. Pulse test

## Main Characteristics

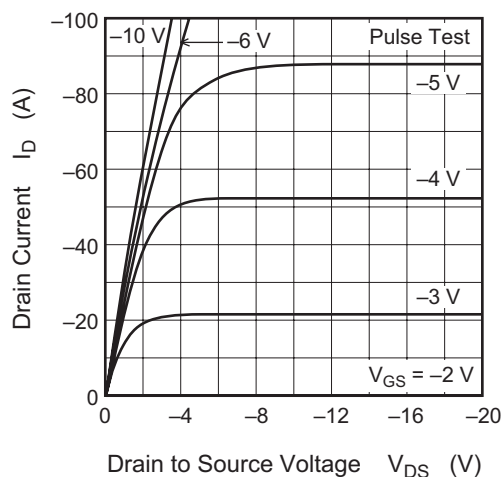
Power vs. Temperature Derating



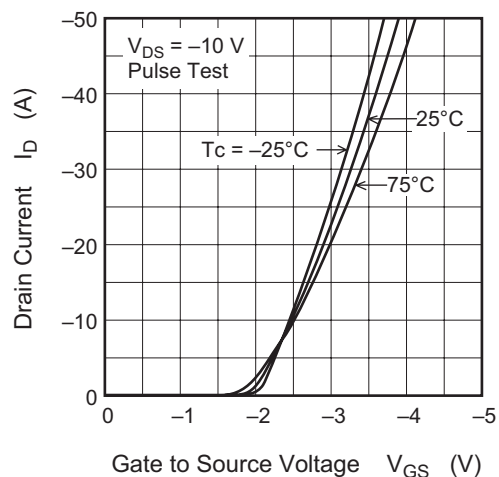
Maximum Safe Operation Area



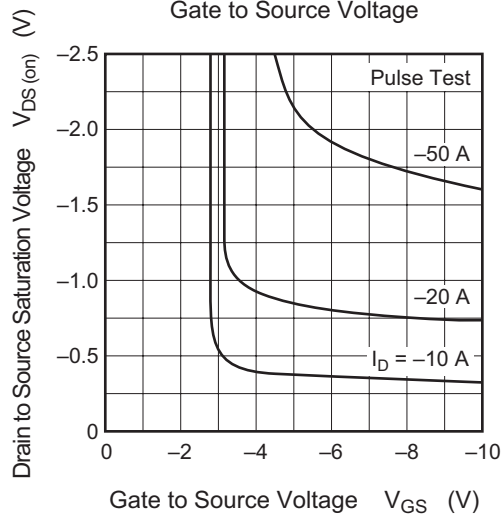
Typical Output Characteristics



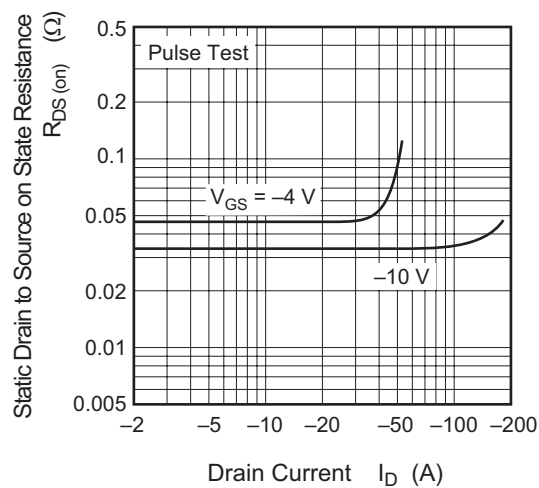
Typical Forward Transfer Characteristics

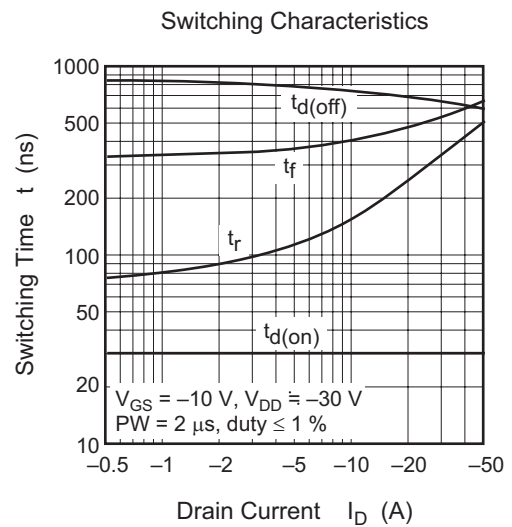
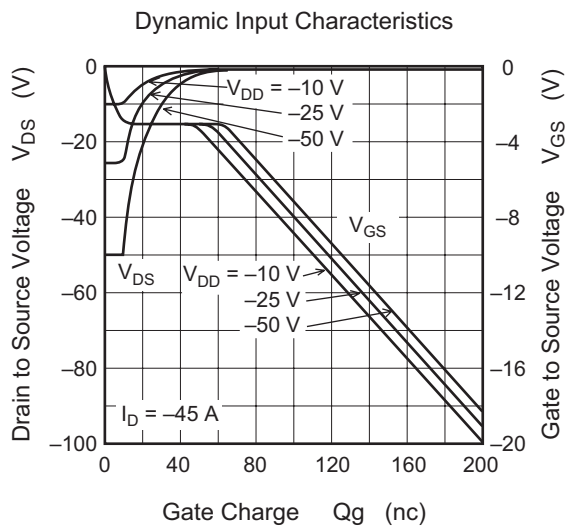
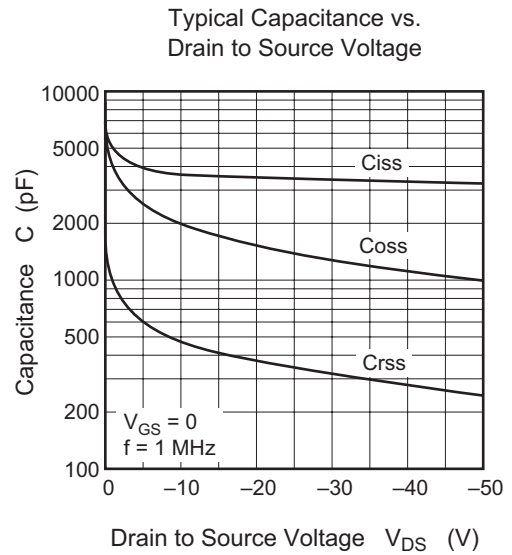
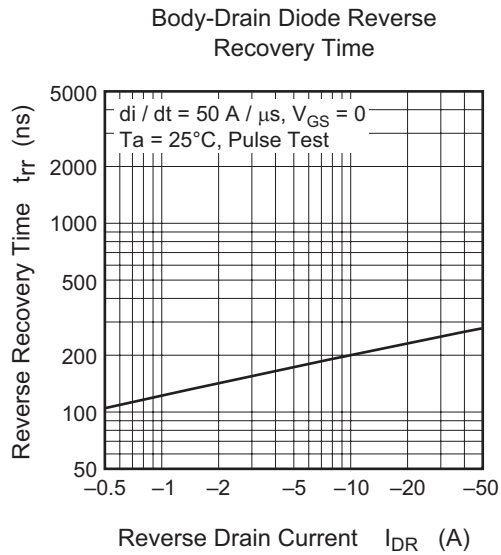
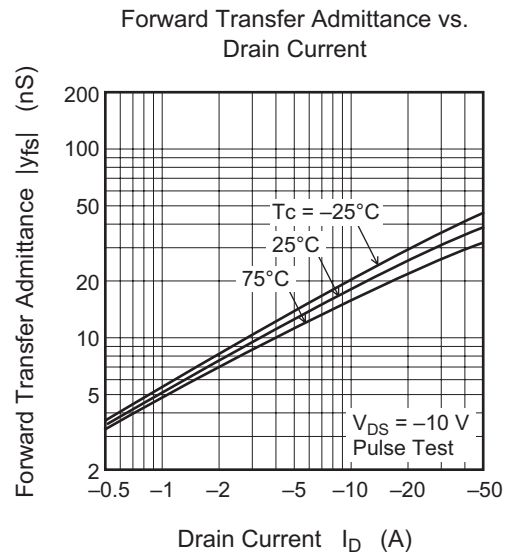
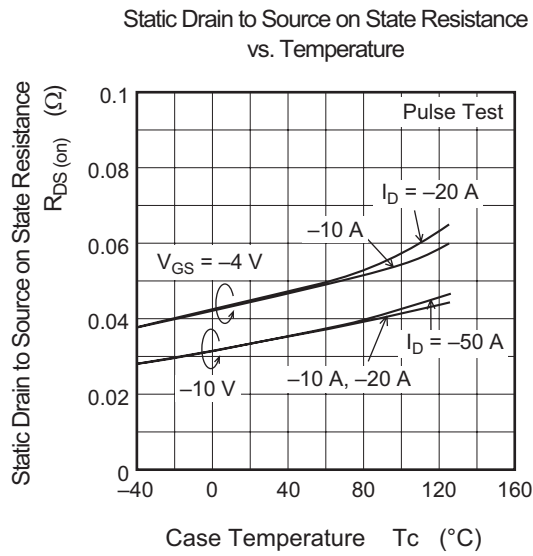


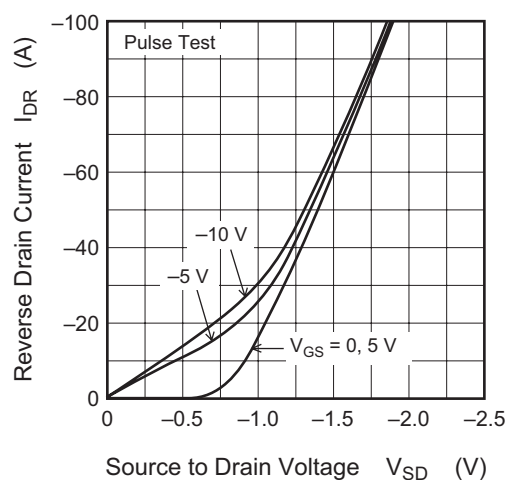
Drain to Source Saturation Voltage vs. Gate to Source Voltage



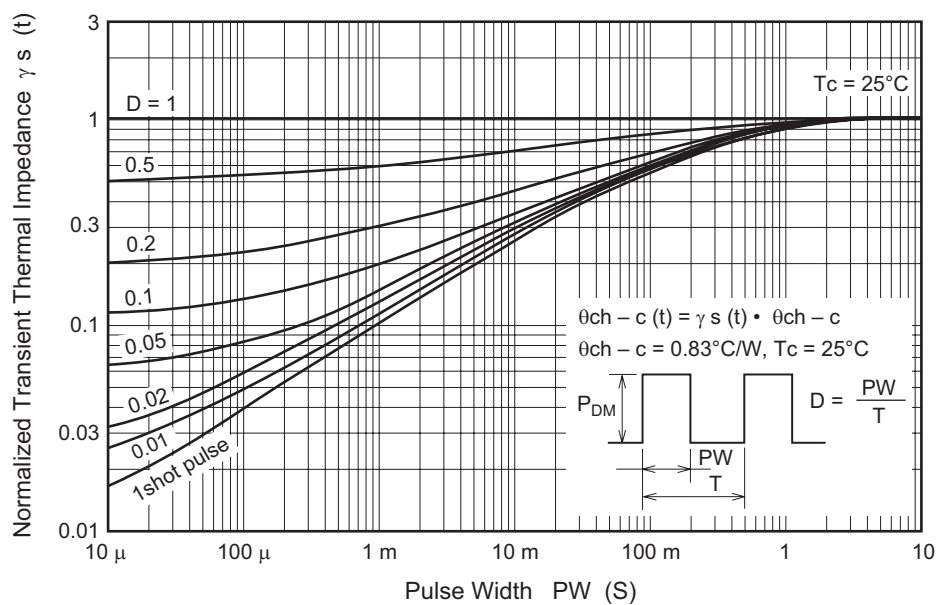
Static Drain to Source on State Resistance vs. Drain Current



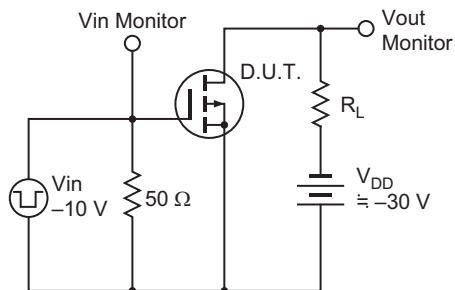


Reverse Drain Current vs.  
Source to Drain Voltage

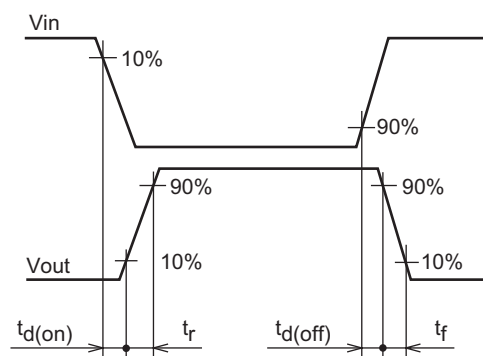
Normalized Transient Thermal Impedance vs. Pulse Width



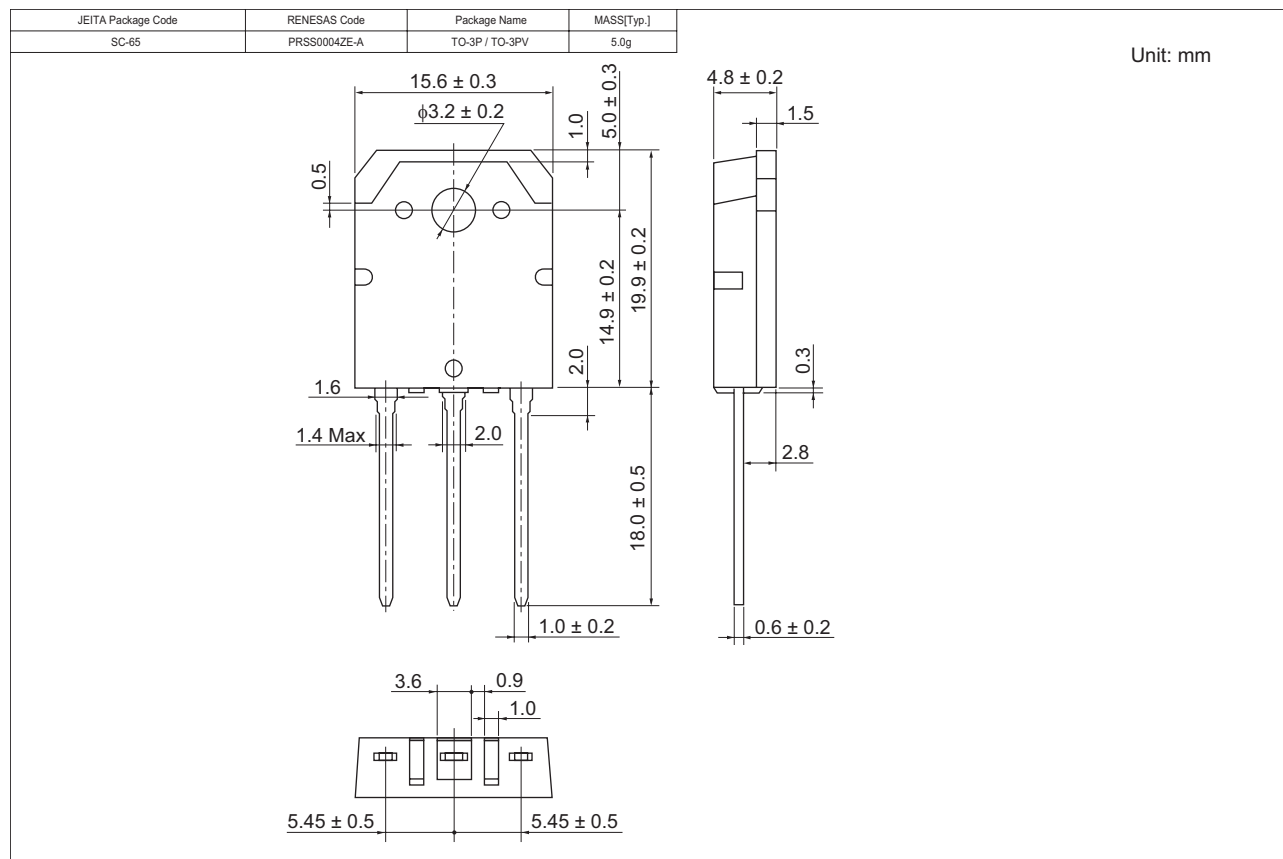
Switching Time Test Circuit



Waveform



## Package Dimensions



## Ordering Information

Part Name	Quantity	Shipping Container
2SJ217-E	30 pcs	Plastic magazine

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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